



**TRANSISTORS, MICROWAVE, SILICON, BIPOLAR,
SMALL SIGNAL**

BASED ON TYPE BFY740B

ESCC Detail Specification No. 5611/011

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DCR No.	CHANGE DESCRIPTION
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1 GENERAL

1.1 SCOPE

This specification details the ratings, physical and electrical characteristics and test and inspection data for the component type variants and/or the range of components specified below. It supplements the requirements of, and shall be read in conjunction with, the ESCC Generic Specification listed under Applicable Documents.

1.2 APPLICABLE DOCUMENTS

The following documents form part of this specification and shall be read in conjunction with it:

- (a) ESCC Generic Specification No. [5010](#)
- (b) [MIL-STD-750](#), Test Methods and Procedures for Semiconductor Devices

1.3 TERMS, DEFINITIONS, ABBREVIATIONS, SYMBOLS AND UNITS

For the purpose of this specification, the terms, definitions, abbreviations, symbols and units specified in ESCC Basic Specification No. [21300](#) shall apply.

1.4 THE ESCC COMPONENT NUMBER AND COMPONENT TYPE VARIANTS

1.4.1 The ESCC Component Number

The ESCC Component Number shall be constituted as follows:

Example: 561101101

- Detail Specification Reference: 5611011
- Component Type Variant Number: 01

1.4.2 Component Type Variants

The component type variants applicable to this specification are as follows:

Variant Number	Based on Type	Die Metallisation	Case	Lead Material and Finish	Weight max g
01	BFY740B	NiPPdAu	Micro-X	G2	0.03
02	BFY740B	TiPtAu	Micro-X	G2	0.03

The lead material and finish shall be in accordance with the requirements of ESCC Basic Specification No. [23500](#).

1.5 MAXIMUM RATINGS

The maximum ratings shall not be exceeded at any time during use or storage.

Maximum ratings shall only be exceeded during testing to the extent specified in this specification and when stipulated in Test Methods and Procedures of the ESCC Generic Specification.

Characteristics	Symbols	Maximum Ratings	Units	Remarks
Collector-Emitter Voltage	V_{CEO}	4 3.5	V	$T_{amb} > 0^{\circ}C$ $T_{amb} \leq 0^{\circ}C$
Collector-Emitter Voltage	V_{CES}	13	V	
Collector-Base Voltage	V_{CBO}	13	V	
Emitter-Base Voltage	V_{EBO}	1.2	V	
Collector Current	I_C	30	mA	
Base Current	I_B	3	mA	Note 1
Power Dissipation	P_{tot}	120	mW	$T_S \leq +125^{\circ}C$ Note 2
Operating Temperature Range	T_{op}	-65 to +175	$^{\circ}C$	T_S
Storage Temperature Range	T_{stg}	-65 to +175	$^{\circ}C$	
Junction Temperature	T_j	+175	$^{\circ}C$	
Thermal Resistance, Junction-to-Soldering Point	$R_{th(j-s)}$	417	$^{\circ}C/W$	
Soldering Temperature	T_{sol}	+250	$^{\circ}C$	Note 3

NOTES:

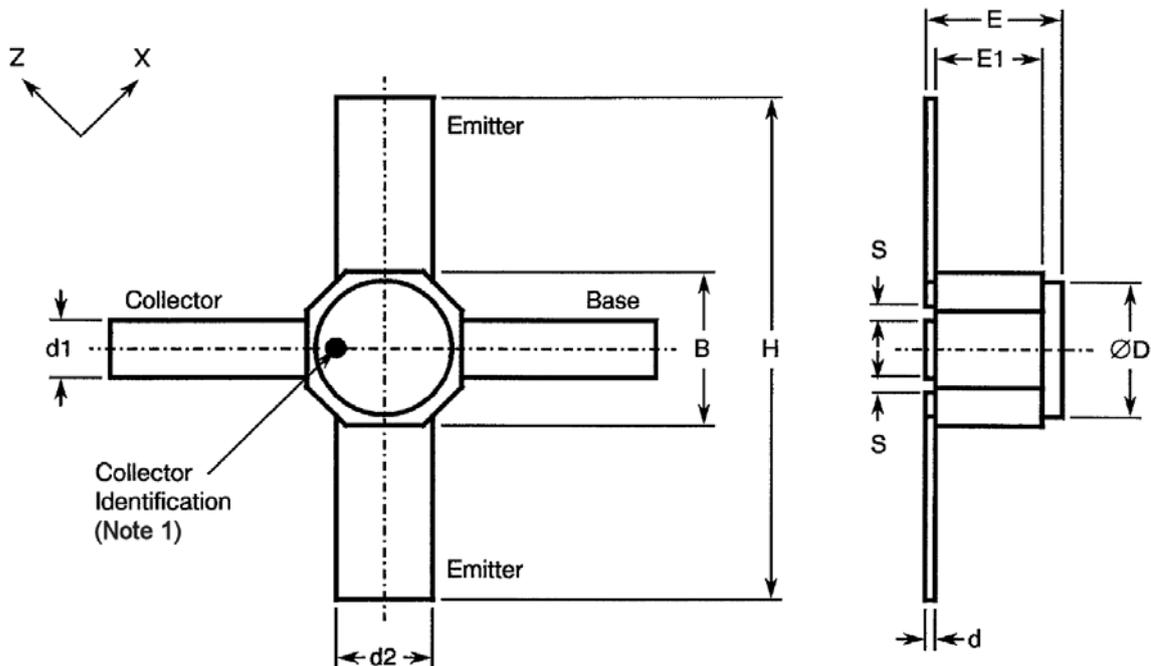
1. Maximum ratings must not be exceeded under any combination of DC ratings and RF voltage/current swings except as specified in Para. 2.5.1 herein.
2. T_S is measured on the collector lead at the soldering point to the PCB. For T_S greater than specified, P_{tot} derates linearly to 0W at $T_S = +175^{\circ}C$.
3. Duration 5 seconds maximum at a distance of not less than 0.5mm from the device body and the same lead shall not be resoldered until 3 minutes have elapsed.

1.6 HANDLING PRECAUTIONS

These devices are susceptible to damage by electrostatic discharge. Therefore suitable precautions shall be employed for protection during all phases of manufacture test, packaging, shipping and handling.

These components are categorised as Class 1 per ESCC Basic Specification No. [23800](#) with a Minimum Critical Path Failure Voltage of 100V.

1.7 PHYSICAL DIMENSIONS AND TERMINAL IDENTIFICATION
Micro-X Package

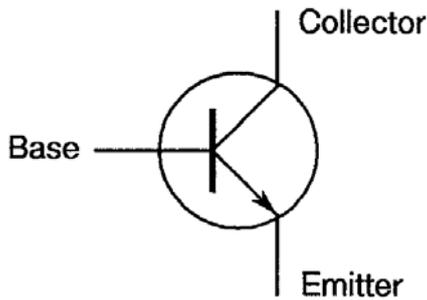


Symbols	Dimensions mm		Notes
	Min	Max	
B	1.68	1.88	2
d	0.07	0.15	3
d1	0.4	0.6	2
d2	0.92	1.12	2
$\varnothing D$	1.55	1.85	
E	0.85	1.25	3
E1	0.66	0.86	3
H	4	4.4	2
S	0.08	0.3	4

NOTES:

1. The Collector terminal is identified by means of a black dot marked on the lid, with the three other terminals identifiable by the component's geometry.
2. Applies in two places.
3. Applies to all leads.
4. Applies in four places.

1.8 FUNCTIONAL DIAGRAM



NOTES:

1. The lid is connected to the Emitter terminal.

1.9 MATERIALS AND FINISHES

Materials and finishes shall be as follows:

- (a) Case
The case shall be hermetically sealed and have a ceramic body with a metal lid.
- (b) Leads
As specified in Para. 1.4.2 Component Type Variants.

2 REQUIREMENTS

2.1 GENERAL

The complete requirements for procurement of the components specified herein are as stated in this specification and the ESCC Generic Specification. Permitted deviations from the Generic Specification, applicable to this specification only, are listed below.

Permitted deviations from the Generic Specification and this Detail Specification, formally agreed with specific Manufacturers on the basis that the alternative requirements are equivalent to the ESCC requirement and do not affect the component's reliability, are listed in the appendices attached to this specification.

2.1.1 Deviations from the Generic Specification

2.1.1.1 *Deviations from Screening Tests for Packaged Components – Chart F3A*

- (a) Radiographic Inspection: shall be performed in the X and Z axes only.

2.1.1.2 *Deviations from Qualification and Periodic Tests for Packaged Components - Chart F4A*

- (a) Mechanical Shock: Not applicable.
- (b) Vibration: Not applicable.
- (c) Constant Acceleration: Not applicable.

2.2 MARKING

The marking shall be in accordance with the requirements of ESCC Basic Specification No. 21700. The information to be marked and the order of precedence shall be as follows:

- (a) Terminal identification.
- (b) The ESCC qualified components symbol (for ESCC qualified components only).
- (c) The ESCC Component Number (see Para. 1.4.1).
- (d) Traceability information.

2.3 DIE SHEAR

In those cases where package clearances are such that a die shear test is not practicable, the die shall be pushed away with a suitable tool. The force required to remove the die need not be recorded. The die attachment area shall be inspected and the component shall be considered acceptable if more than 50% of the semiconductor material remains.

2.4 TERMINAL STRENGTH

The test conditions for terminal strength, tested as specified in the ESCC Generic Specification, shall be as follows:

- Test Condition A, tension, with a force of 2.23N and a duration of 5s.

2.5 ELECTRICAL MEASUREMENTS AT ROOM, HIGH AND LOW TEMPERATURES

2.5.1 Room Temperature Electrical Measurements

The measurements shall be performed at $T_{amb} = +25 \pm 3^{\circ}C$.

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Emitter Cut-off Current 1	I_{CES1}	3041	Bias Condition C $V_{CE} = 13V$	-	1000	nA
Collector-Emitter Cut-off Current 2	I_{CES2}	3041	Bias Condition C $V_{CE} = 10.5V$	-	100	nA
Collector-Emitter Cut-off Current 3	I_{CES3}	3041	Bias Condition C $V_{CE} = 5V$	-	20	nA
Collector-Emitter Cut-off Current 4	I_{CEX}	3041	$V_{CE} = 4V, I_B = 100nA$ Variant 01: Variant 02:	20 20	100 150	μA
Emitter-Base Cut-off Current 1	I_{EBO1}	3061	Bias Condition D $V_{EB} = 1.2V$	-	5	μA
Emitter-Base Cut-off Current 2	I_{EBO2}	3061	Bias Condition D $V_{EB} = 500mV$	-	100	nA
Forward-Current Transfer Ratio 1	h_{FE1}	3076	$V_{CE} = 3V, I_C = 20mA$	185	380	-
Forward-Current Transfer Ratio 2	h_{FE2}	3076	$V_{CE} = 3V, I_C = 20\mu A$	240	690	-
Base-Emitter Forward Voltage	V_{FBE}	4011	$I_B = 12mA, I_C = 0A$ Note 1	-	960	mV
Collector-Emitter Capacitance	C_{CE}	3236	$V_{CE} = 2V, I_B = 0A, f = 1MHz$ Common Base Configuration	-	0.5	pF
Collector-Base Capacitance	C_{CB}	3236	$V_{CB} = 2V, I_E = 0A, f = 1MHz$ Common Emitter Configuration	-	0.12	pF
Emitter-Base Capacitance	C_{EB}	3236	$V_{EB} = 500mV, I_C = 0A, f = 1MHz$ Common Collector Configuration	-	0.8	pF
Insertion Power Gain at 1.8GHz	$ S_{21} ^2_{1.8}$	-	$f = 1.8GHz, V_{CE} = 3V, I_C = 20mA$ Notes 2, 3	22	-	dB
Insertion Power Gain at 6GHz	$ S_{21} ^2_6$	-	$f = 6GHz, V_{CE} = 3V, I_C = 20mA$ Notes 2, 3	12	-	dB
Maximum Available / Stable Gain at 1.8GHz	MAG / $MSG_{1.8}$	-	$f = 1.8GHz, V_{CE} = 3V, I_C = 20mA$ Notes 2, 3, 4	24	-	dB
Maximum Available / Stable Gain at 6GHz	MAG / MSG_6	-	$f = 6GHz, V_{CE} = 3V, I_C = 20mA$ Notes 2, 3, 4	17	-	dB
Noise Figure at 1.8GHz	$NF_{1.8}$	-	$f = 1.8GHz, V_{CE} = 3V, I_C = 8mA$ Notes 3, 5, 6	-	0.75	dB
Noise Figure at 6GHz	NF_6	-	$f = 6GHz, V_{CE} = 3V, I_C = 8mA$ Notes 3, 5, 6	-	1.15	dB

NOTES:

1. Pulsed measurement, pulse duration < 1s, single pulse. I_B may exceed that specified in Para. 1.5 Maximum Ratings.
2. Measured in a 50Ω system using a suitable network analyser.
3. Small signal measurement.
4. MAG if K ≥ 1; MSG if K < 1.
5. Input tuned for NF_{min}.
6. Measurements shall be performed on a sample of 15 components with the maximum allowed limit reduced by 0.07dB. In the event of any failure a 100% inspection shall be performed and the specified limit shall apply.

2.5.2 High and Low Temperatures Electrical Measurements

Characteristics	Symbols	MIL-STD-750 Test Method	Test Conditions	Limits		Units
				Min	Max	
Collector-Emitter Cut-off Current 2	I _{CES2}	3041	T _{amb} = +150 (+0 -5)°C Bias Condition C V _{CE} = 10.5V, Note 1	-	5	μA
Collector-Emitter Cut-off Current 3	I _{CES3}	3041	T _{amb} = +150 (+0 -5)°C Bias Condition C V _{CE} = 5V, Note 1	-	1	μA
Emitter-Base Cut-off Current 1	I _{EBO1}	3061	T _{amb} = +150 (+0 -5)°C Bias Condition D V _{EB} = 1.2V, Note 1	-	50	μA
			T _{amb} = -55 (+5 -0)°C Bias Condition D V _{EB} = 1.2V, Note 2	-	5	μA
Emitter-Base Cut-off Current 2	I _{EBO2}	3061	T _{amb} = +150 (+0 -5)°C Bias Condition D V _{EB} = 500mV, Note 1	-	1	μA
Forward-Current Transfer Ratio 1	h _{FE1}	3076	T _{amb} = +150 (+0 -5)°C V _{CE} = 3V, I _C = 20mA, Note 1	85	250	-
			T _{amb} = -55 (+5 -0)°C V _{CE} = 3V, I _C = 20mA, Note 2	150	400	-

NOTES:

1. Measurements shall be performed on a sample of 5 components. In the event of any failure, a 100% inspection shall be performed.
2. Measurements shall be performed on a sample of 5 assembled components per wafer. In the event of any failure, a 100% inspection shall be performed.

2.6 PARAMETER DRIFT VALUES

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +25 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.5.1 Room Temperature Electrical Measurements.

The drift values (Δ) shall not be exceeded for each characteristic specified. The corresponding absolute limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value (1) Δ	Absolute		
			Min	Max	
Collector-Emitter Cut-off Current 2	I_{CES2}	± 20 or (2) +100/-50%	-	100	nA
Collector-Emitter Cut-off Current 3	I_{CES3}	± 5 or (2) +100/-50%	-	20	nA
Emitter-Base Cut-off Current 1	I_{EBO1}	± 0.5 or (2) +100/-50%	-	5	μA
Emitter-Base Cut-off Current 2	I_{EBO2}	± 20 or (2) +100/-50%	-	100	nA
Forward-Current Transfer Ratio 1	h_{FE1}	$\pm 10\%$	185	380	-
Base-Emitter Forward Voltage	V_{FBE}	± 20 (3)	-	960	mV

NOTES:

- $\Delta 1 = \Delta 2$.
- Whichever is greater.
- The total change over both Burn-in 1 and Burn-in 2 referred to the initial value made prior to Burn-in 1.

2.7 **INTERMEDIATE AND END-POINT ELECTRICAL MEASUREMENTS**

Unless otherwise specified, the measurements shall be performed at $T_{amb} = +25 \pm 3^{\circ}C$.

The test methods and test conditions shall be as per the corresponding test defined in Para. 2.5.1 Room Temperature Electrical Measurements.

The limit values for each characteristic shall not be exceeded.

Characteristics	Symbols	Limits			Units
		Drift Value Δ	Absolute		
			Min	Max	
Collector-Emitter Cut-off Current 2	I_{CES2}	± 20 or (1) +100/-50%	-	100	nA
Collector-Emitter Cut-off Current 3	I_{CES3}	± 5 or (1) +100/-50%	-	20	nA
Emitter-Base Cut-off Current 1	I_{EBO1}	± 0.5 or (1) +100/-50%	-	5	μA
Emitter-Base Cut-off Current 2	I_{EBO2}	± 20 or (1) +100/-50%	-	100	nA
Forward-Current Transfer Ratio 1	h_{FE1}	$\pm 10\%$	185	380	-
Base-Emitter Forward Voltage	V_{FBE}	± 20	-	960	mV

NOTES:

1. Whichever is greater.

2.8 BURN-IN 1 CONDITIONS

Characteristics	Symbols	Test Conditions (Note 1)	Units
Soldering Point Temperature	T_S	+150 (+0 -5)	°C
Collector-Emitter Voltage	V_{CES}	10.5	V
Base-Emitter Voltage	V_{BE}	0	V

NOTES:

1. Maximum ratings shall not be exceeded during power up and power down sequences.

2.9 BURN-IN 2 CONDITIONS

Characteristics	Symbols	Test Conditions (Notes 1, 2)	Units
Soldering Point Temperature	T_S	$\geq +125$	°C
Junction Temperature	T_j	+175 (+0 -5)	°C
Power Dissipation	P_{tot}	$\leq P_{tot}$ (see Para. 1.5)	mW
Collector-Emitter Voltage	V_{CE}	3.5	V

NOTES:

1. Maximum ratings shall not be exceeded during power up and power down sequences.
2. T_S and/or P_{tot} shall be adjusted to attain the specified T_j .

2.10 OPERATING LIFE CONDITIONS

The conditions shall be as specified in Para. 2.9 Burn-in 2 Conditions.

APPENDIX A
AGREED DEVIATIONS FOR INFINEON TECHNOLOGIES AG (D)

Items Affected	Description of Deviations
Para. 2.1.1 Deviations from Generic Specification: Special In-Process Controls - Chart F2	<p>Internal Visual Inspection: shall include verification of the length, height and shape of the wire bonding.</p> <p>Bond Strength: the following pre-seal bond strength shall apply:</p> <ul style="list-style-type: none"> • 0.015N minimum <p>Die Shear: if Para. 2.3 does not apply, the following shear strength may be applied:</p> <ul style="list-style-type: none"> • 0.4N minimum <p>Dimension Check: may be performed during Chart F3A testing.</p>
Para. 2.1.1.1 Deviations from Screening Tests for Packaged Components - Chart F3A	<p>Temperature Cycling: shall be replaced by a Thermal Shock test in accordance with MIL-STD-202, Test Method 107, Test Condition B, 20 cycles.</p> <p>Radiographic Inspection: shall not be performed.</p>
Para. 2.1.1.2 Deviations from Qualification and Periodic Tests for Packaged Components - Chart F4A	<p>Temperature Cycling: shall be replaced by a Thermal Shock test in accordance with MIL-STD-202, Test Method 107, Test Condition B, 100 cycles.</p> <p>Assembly Capability Subgroup tests: in addition to the permitted use of empty packages or electrical rejects as test samples, components rejected during the following Screening Tests:</p> <ul style="list-style-type: none"> • Radiographic Inspection • Seal • External Visual Inspection <p>may be used on the condition that the cause for rejection has no possible impact on the tests, and they have been subjected to the same screening as the packages of the assembly lot with which they are associated.</p> <p>Bond Strength: the following post-seal bond strength shall apply:</p> <ul style="list-style-type: none"> • 0.012N minimum <p>Die Shear: if Para. 2.3 does not apply, the following shear strength may be applied:</p> <ul style="list-style-type: none"> • 0.4N minimum
Para. 2.1.1 Deviations from Generic Specification: Final Customer Source Inspection	<p>Final Customer Source Inspection shall be limited to witnessing of the DC and 1MHz parameters specified in Para. 2.5.1 Room Temperature Electrical Measurements.</p>
Para. 2.1.1 Deviations from Generic Specification: Data Documentation	<p>Additional Documentation and Wafer Lot Acceptance Data: if Wafer Lot Acceptance Data is stipulated in the Purchase Order, such data will not be delivered but will be available for review at Infineon Technologies AG.</p>